

Absorption correction for flat specimen with QUATTRO-TRANS

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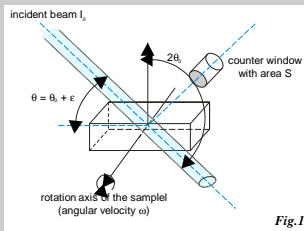
Project: The Multiple-Detector System for the powder diffractometer at beamline B2

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Introduction

For an accurate structure analysis it is of great importance to treat properly the absorption effect, which largely influences the intensities of the diffracted beam. At the beamline B2 an multiple-detectors system (MDS) [1, 2] with four analyser diffractometers is used three of them (detector 2, 3 and 4) are operating under asymmetrical diffraction condition. Using flat specimen an absorption correction of the raw data is necessary. We developed a routine for this correction which is implemented in the program QUATTRO-TRANS [3]. Based on the formula of James [4] the geometrical case of asymmetrical diffraction condition is introduced.

Theory



The area S of the counter window is perpendicular to the reflected beam when the angle of reflection is θ_0 . The total energy E , passing through the area S which is perpendicular to the reflected beam depends on the intensity of the incident beam I_0 , the time $d\epsilon/\omega$ to rotate through the very small angular range $d\epsilon$ and the scattering power $R(\epsilon)$; (I_r/I_0). According to fig. 1 this gives

$$E_s = I_0 \cdot S \int_{\text{angle}} R(\epsilon) \frac{d\epsilon}{\omega} \quad (1)$$

The integration of the scattering power $R(\epsilon)$ gives the volume Δv , (fig.2) and the factor Q which describes the scattering power $R(\epsilon)$ in direction of $2\theta_0$ and dependent on the wavelength λ .

$$\frac{E_s \cdot \omega}{I_0} = \frac{N^2 \lambda^3}{\sin^2 2\theta_0} |F|^2 \left(\frac{e^2}{m c^2} \right)^2 \cdot \frac{dx S}{\sin \theta_0} \quad (2)$$

$$\frac{E_s \cdot \omega}{I_0} = Q \cdot \Delta v_s \quad (3)$$

The sectional area S_0 and the height SH of the incident beam are constant and independent on the Bragg angle θ_0 . It is significant to note that a small Bragg angle θ_0 extends the volume Δv , (the number of excited electrons increases) but the density of the electrons does not change. In the case of **symmetrical diffraction** condition the scattering vector h is perpendicular to the surface of the sample plate (fig. 3). The path length of the incident and diffracted beam are equal; $z/\sin \theta_0$. The integrated intensity is given by (4). Particular for the MDS the **asymmetrical diffraction** condition (fig. 4) means for the detectors 2, 3 and 4: the incident beam falls with an glancing angle α (θ) on the surface of the sample and the detectors receive the diffracted beams with three different glancing angles β (det. 2, θ +offset 1; det. 3, θ +offset 2; det. 4, θ +offset 3). QUATTRO-TRANS works on the least square routine with a reference data set (raw data of the first detector, symmetrical diffraction geometry) and the data sets of the three detectors in asymmetrical diffraction geometry. The fixed parameter of the fit is the total linear absorption coefficient μ . The scale, the offsets of the three detectors in asymmetrical diffraction geometry and the distance the beam travels through a homogeneous isotropic material are refined by the fit. The integrated intensity is given by (5).

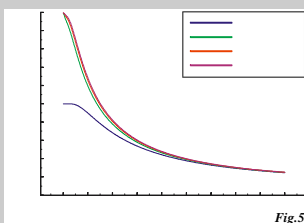
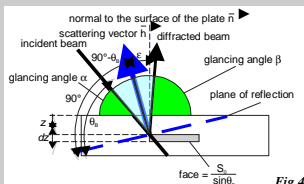
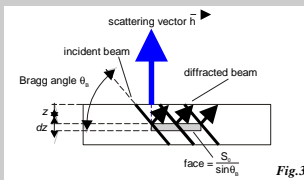
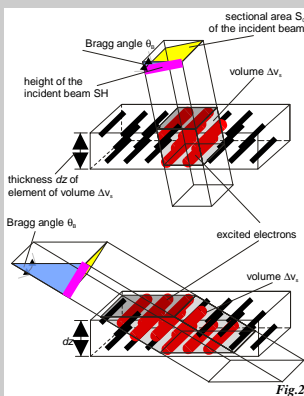
$$\frac{E_s \cdot \omega}{I_0 \cdot S_0} = \frac{Q}{2\mu} \cdot \left[1 - \exp^{-2 \frac{\mu \cdot D_s}{\sin \theta_0}} \right] \quad (4)$$

$$\frac{E_s \cdot \omega}{I_0 \cdot S_0} = \frac{Q}{\mu \cdot \left(1 + \frac{\sin \alpha}{\sin \beta} \right)} \cdot \left[1 - \exp^{-\left(\frac{1}{\sin \alpha} + \frac{1}{\sin \beta} \right) \cdot D} \right] \quad (5)$$

For each data set a transmission function is calculated. In fig. 5 the transmission functions of SiO_2 are shown ($\mu = 96 \text{ l/cm}$, $D = 0.001 \text{ cm}$). The reference data set (detector 1; TRA, (6)) differs from the other data sets (TRV, (7)) caused by the offsets.

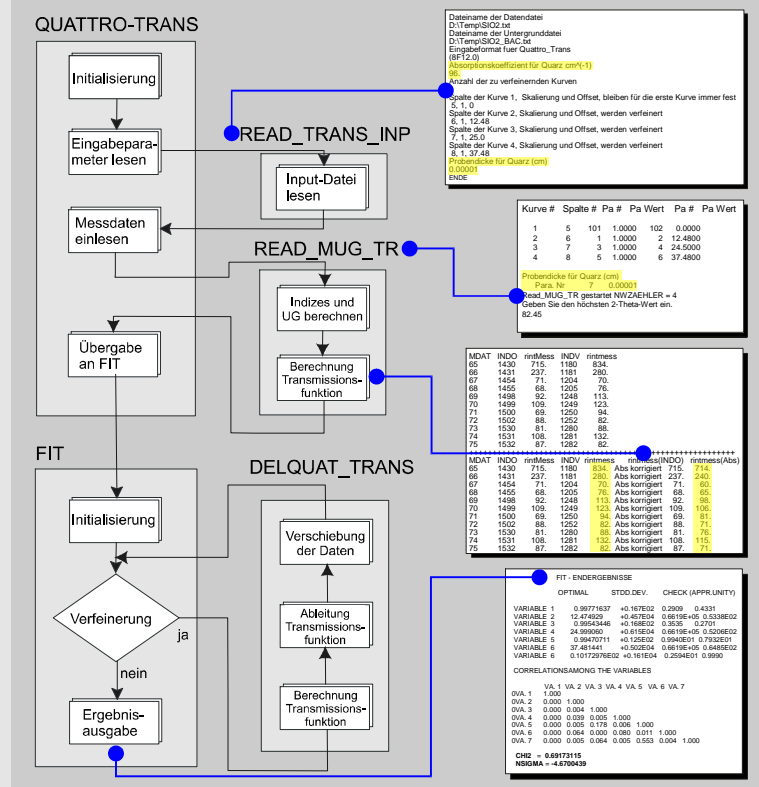
$$TRA = \frac{1}{2\mu} \cdot \left[1 - \exp^{-\mu D_s \left(\frac{2}{\sin \alpha} \right)} \right] \quad (6)$$

$$TRV = \frac{1}{\mu \left[1 + \frac{\sin \alpha}{\sin \beta} \right]} \cdot \left[1 - \exp^{-\mu D_s \left(\frac{1}{\sin \alpha} + \frac{1}{\sin \beta} \right)} \right] \quad (7)$$

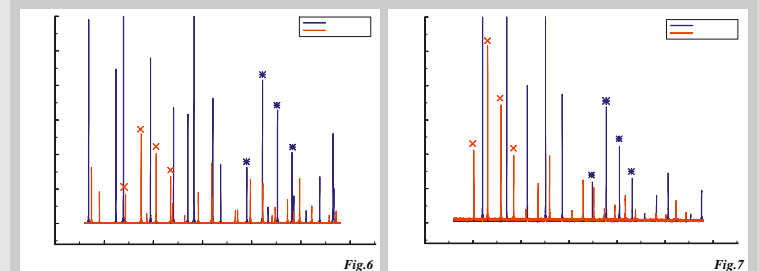


Transmission functions of SiO_2 data. The blue curve shows the reference data set (detector 1). The transmission of the other detectors operating under asymmetrical diffraction geometry is higher at small diffraction angles.

QUATTRO-TRANS



Raw data and synthetic data



Raw data of $\text{LaB}_6 + \text{Si}$. The blue curve shows the reference data set (detector 1) and the red curve the data of detector 3. The marked peaks are equal reflexions. Compare the maximum cps of these peaks with those in fig. 7.

References

- [1] W.-H.Kaps, J.Ihringer, W.Prandl, M.Schilling, The Multiple-Detector System for the powder diffractometer at beamline B2 (HASYLAB), XVIIth IUCr Congress Glasgow, P13.01.016, (1999), S.239
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- [4] R.W. James, "The Optical Principles of the Diffraction of X-Rays" London: Bell, 1967 (The Crystallin State - VOL II), S. 46 ff.
- [5] J. Ihringer, A quantitative measure for the goodness of fit in profile refinements with more than 20 degrees of freedom, J. Appl. Cryst. (1995), 28, 618-619

Acknowledgement

We acknowledge financial support by the BMBF (05SM8VTA3).